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Vishay Siliconix

# Automotive P-Channel 20 V (D-S) 175 °C MOSFET



Marking Code: 8S

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-20			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.115			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.205			
I <sub>D</sub> (A)	-3.2			
Configuration	Single			

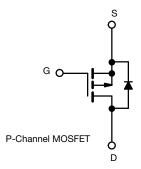
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified d
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2351ES (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage		$V_{DS}$	-20	V		
Gate-source voltage		$V_{GS}$	± 12	V		
Continuous drain current	T <sub>C</sub> = 25 °C		-3.2			
Continuous drain current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-1.8			
Continuous source current (diode conduction)	I <sub>S</sub>	-2.5	Α			
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	-12.7				
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-6			
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	1.8	mJ		
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	2	W		
	T <sub>C</sub> = 125 °C	- P <sub>D</sub>	0.67	VV		
Operating junction and storage temperature rar	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	$R_{thJA}$	175	°C/W	
Junction-to-foot (drain)		$R_{thJF}$	75	G/ <b>VV</b>	

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static					L	L	ı
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = -250 \mu A$		-20	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1.0	-1.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 12 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 175 °C	-	-	-150	1
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -4.5 V	$V_{DS} \ge 5 V$	-8	-	-	Α
		$V_{GS} = -4.5 \text{ V}$	I <sub>D</sub> = -2.4 A	-	0.080	0.115	
Duning and an attack and interest of	Б	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -2.4 A, T <sub>J</sub> = 125 °C	-	-	0.168	Ω
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -2.4 A, T <sub>J</sub> = 175 °C	-	-	0.196	
		V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -1.8 A	-	0.150	0.205	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.4 A		6	-	S
Dynamic <sup>b</sup>							•
Input capacitance	C <sub>iss</sub>			-	265	330	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = -10 \text{ V, f} = 1 \text{ MHz}$	-	75	94	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	50	63	
Total gate charge <sup>c</sup>	Qg			-	3.4	5.5	
Gate-source charge c	Q <sub>gs</sub>	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_{D} = -2.4 \text{ A}$	-	0.6	-	nC
Gate-drain charge c	$Q_{gd}$			-	1.1	=.	
Gate resistance	R <sub>g</sub>	f = 1 MHz		4.8	9.6	14.4	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	20	30	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -10 V, $R_L$ = 5.21 $\Omega$ $I_D$ $\cong$ -1.9 A, $V_{GEN}$ = -4.5 V, $R_g$ = 1 $\Omega$		-	18	27	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	19	28	
Fall time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Char	acteristics						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-12.7	Α
		I <sub>F</sub> = -2 A, V <sub>GS</sub> = 0					

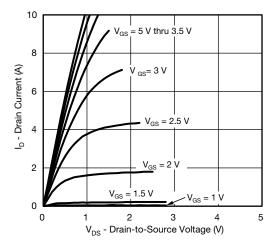
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

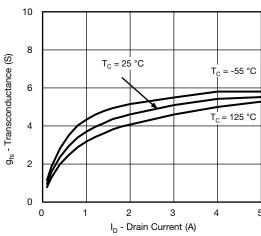
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



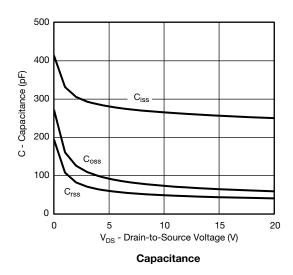
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

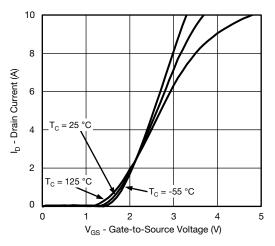


#### **Output Characteristics**

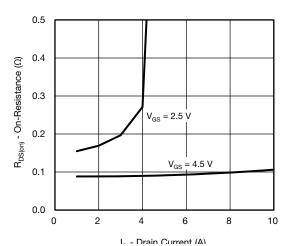


#### Transconductance

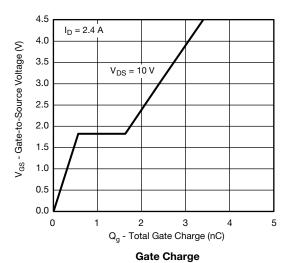




#### **Transfer Characteristics**

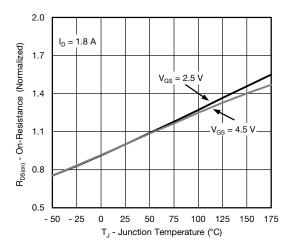


On-Resistance vs. Drain Current

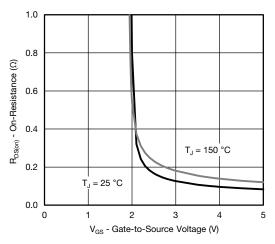




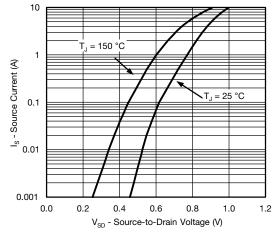
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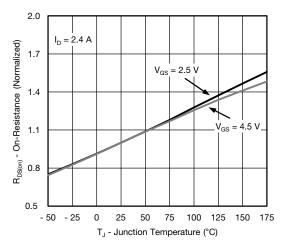
On-Resistance vs. Junction Temperature (1.8 A)



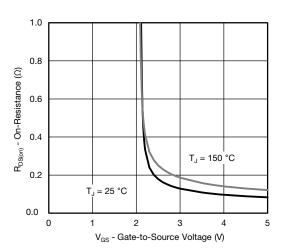
On-Resistance vs. Gate-to-Source Voltage (1.8 A)



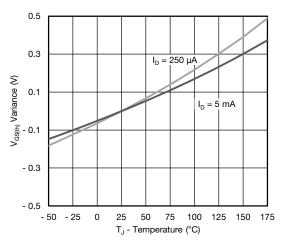
Source-Drain Diode Forward Voltage



On-Resistance vs. Junction Temperature (2.4 A)



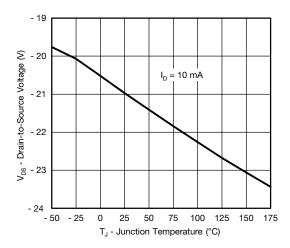
On-Resistance vs. Gate-to-Source Voltage (2.4 A)



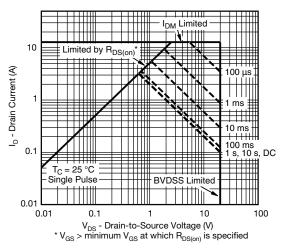
**Threshold Voltage** 



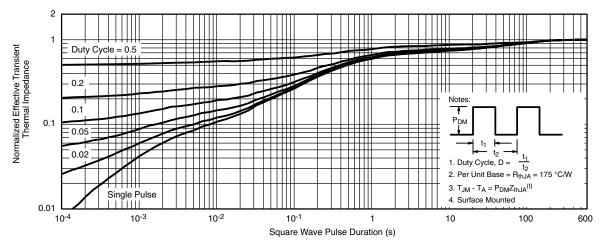
### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Drain Source Breakdown vs. Junction Temperature



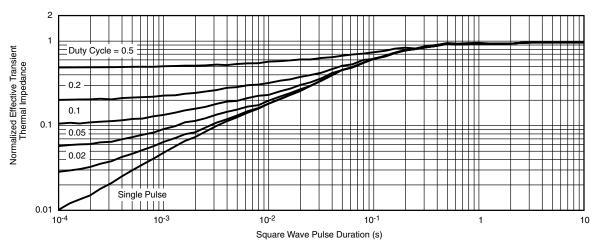
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part

pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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### SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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